

Plasma Dicing “The Next Normal”

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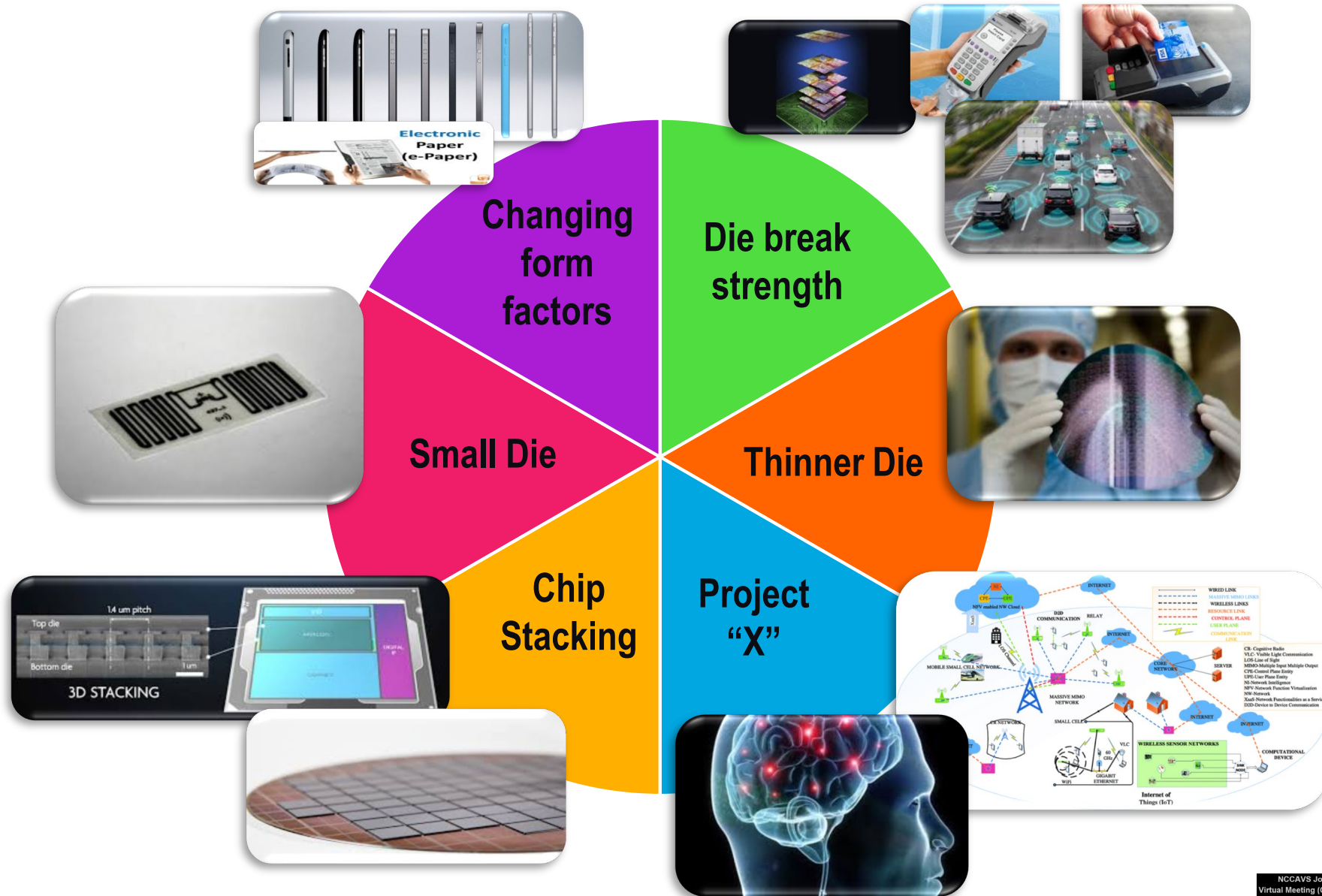
**NCCAUS Joint Users Group
Virtual Meeting (CMPUG, PAG, TFUG)
"Advanced Packaging Technology"
June 10, 2020**

10th June 2020

Content

- Device trends & how they relate to wafer singulation
- Benefits of plasma dicing
- Integration is Key
- SiP
- Examples of Implementation
- Summary
- Q&A

Device Trends – Distributed; Mobile; SiP; At the point of interaction;.....



Benefits of Plasma Dicing



No Damage

- Chemical etch
- No chips, cracks
- No particles
- Controlled sidewall
- No heat zones in Si
- High Etch Rates
- Parallel Process
- Thin Wafers <math><50\mu\text{m}</math>



Flexible Layouts

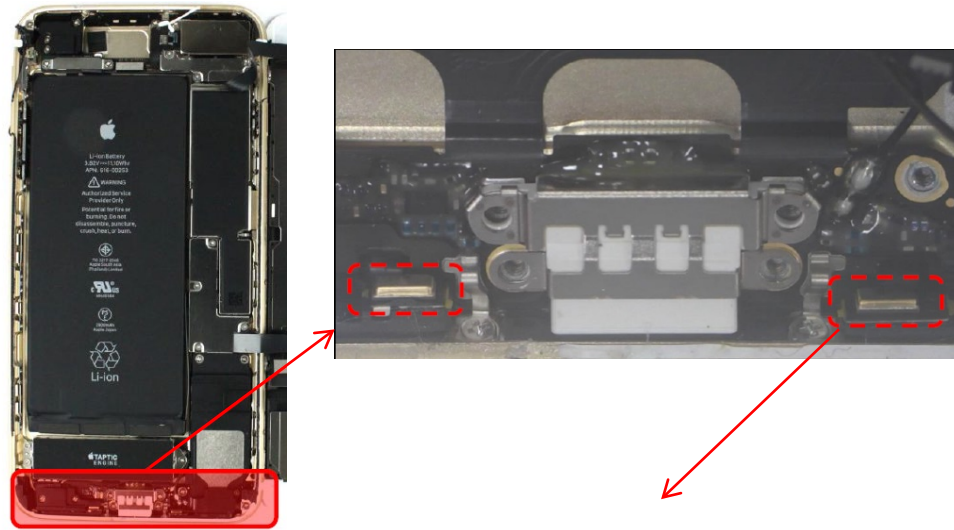
- Kerfs <math><10\mu\text{m}</math>
- Non-orthogonal
- No EE
- Free die shape
- Great for MPW



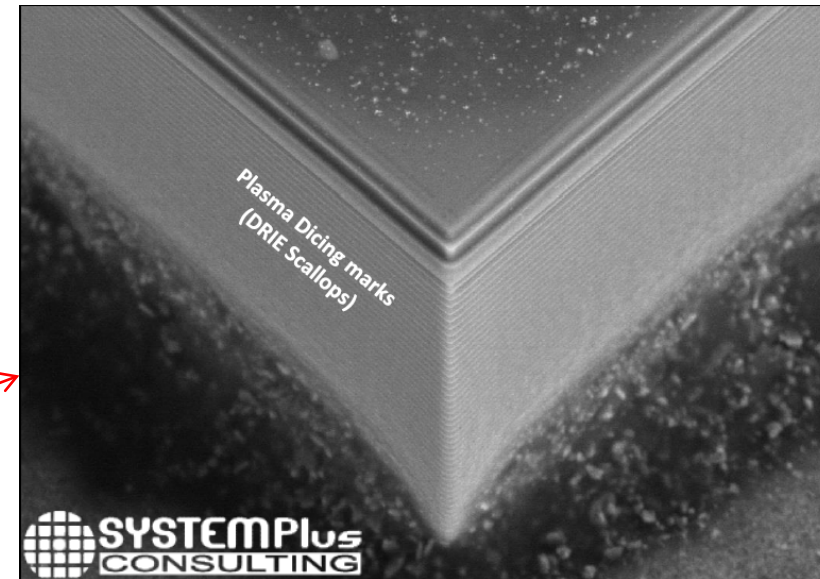
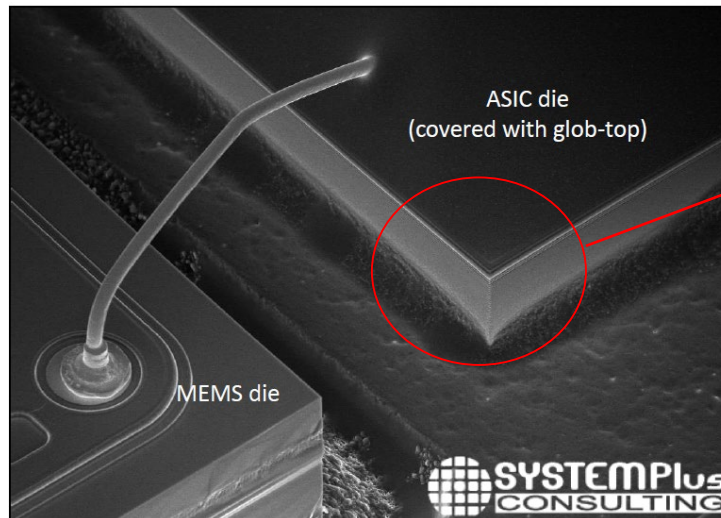
“Front-End” for the “Back-End”

- Clean process
- Process control
- Endpoint
- Wafer Monitoring
- No consumables
- Repeatable
- Consistent
- Cluster platforms

Plasma Dicing already in iPhones



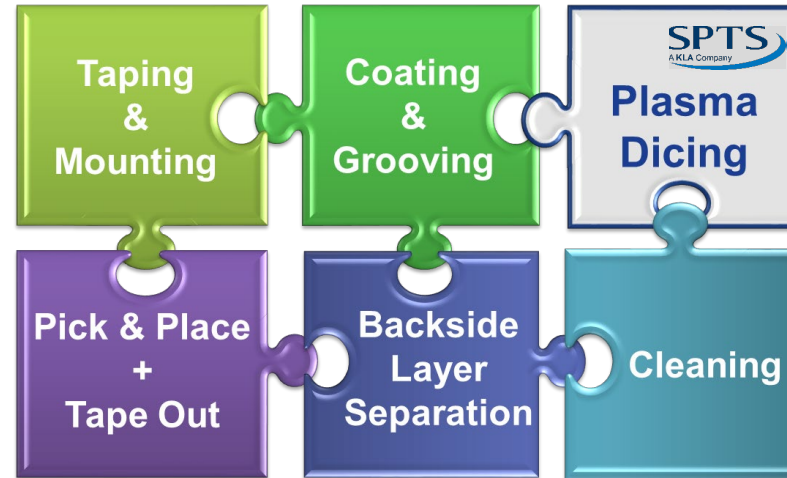
Knowles microphone



Microphone by Tier#1 IDM
ASIC by European Foundry
Dicing by SPTS Rapier PM

Integration is Key

- “Whole Flow” approach established as “Best Practice”



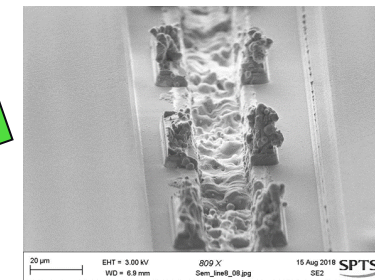
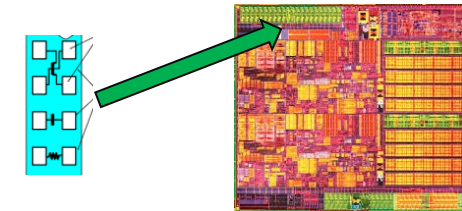
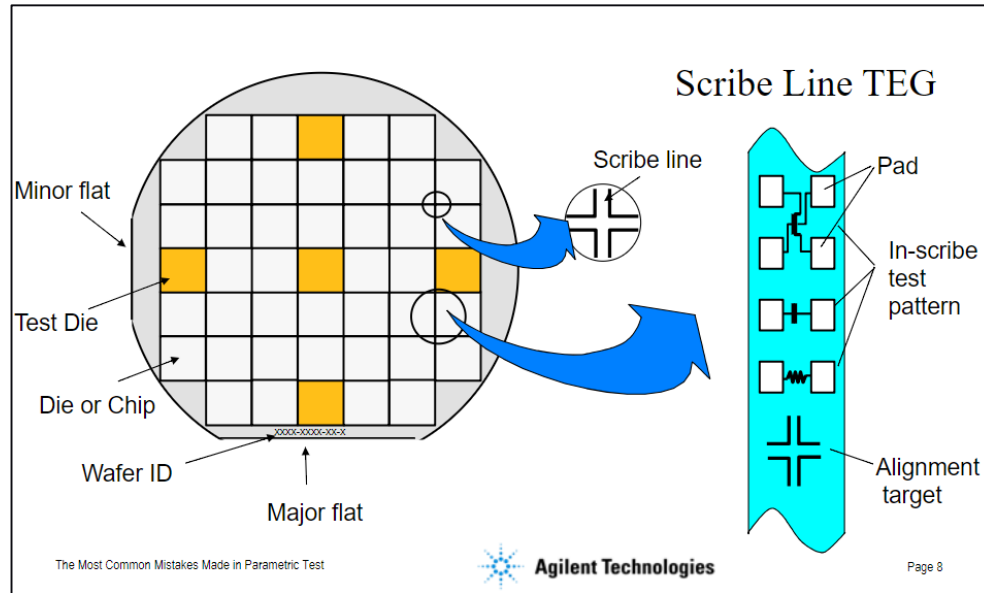
- Collaborations & co-working across back-end community
 - LASER Grooving/Coatings OR Design for Plasma Dicing
 - Tapes
 - Dry Strip or Wet Chemistries
 - Backside Layer Treatment
- Plasma Dicing cannot be treated in isolation

Dicing Highways

Busier than lanes



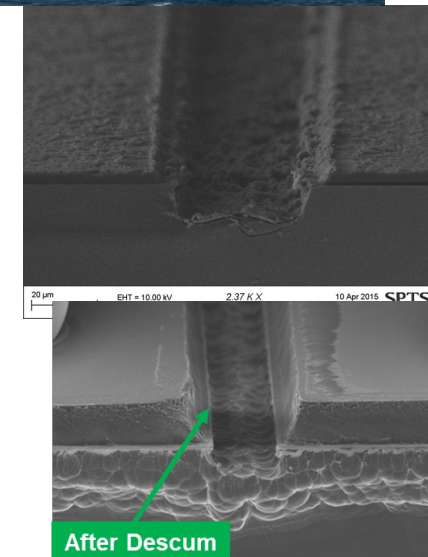
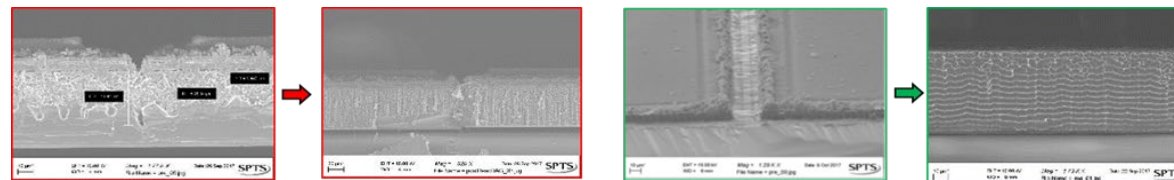
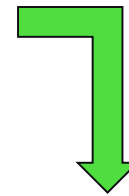
- Key demand
 - **We need compatible & defined features to etch**
- Dicing Lanes are not empty !
 - Metals & Dielectrics – not wholly compatible with plasma DAG
- Options for management of TEGs
 - **“Move or Groove”**



Integration

“Grooving”

- LASER Grooving has become a popular approach
 - Requires coating to protect die, define lanes
 - Not a catch-all solution
- Coating selection is important
 - Selective to etch chemistry
 - Post-etch removal
- LASER clears lanes, but there can be side effects
 - Recast, snow-plough, bow-wave
- Sympathetic process tuning required
 - Good Groove = Good Singulation
 - Use etch conditions to remove residues from Si surface
 - “Descum” – just as we do in the compound world

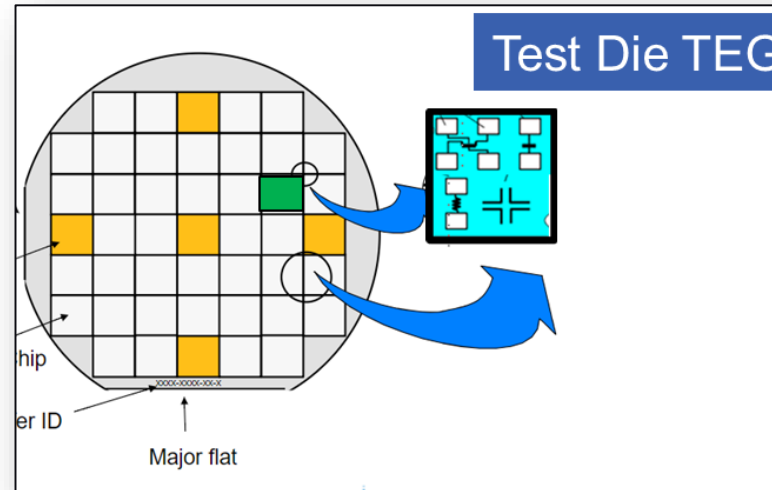


Process integration is critical, hardware integration is not

Integration

“Moving”

- Consider Backend (BE) at the start of design process
 - Narrow lanes can release real estate; die layout & shapes
 - Narrow lanes cannot host TEGs
 - TEG Die to accommodate for test structures, alignment marks can solve this



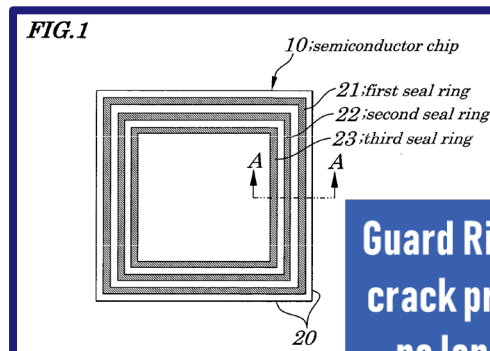
- Designers will need to know if product will be plasma diced
 - Process flow architecture to accommodate shift TEG Die

Design for Manufacture & Test is required

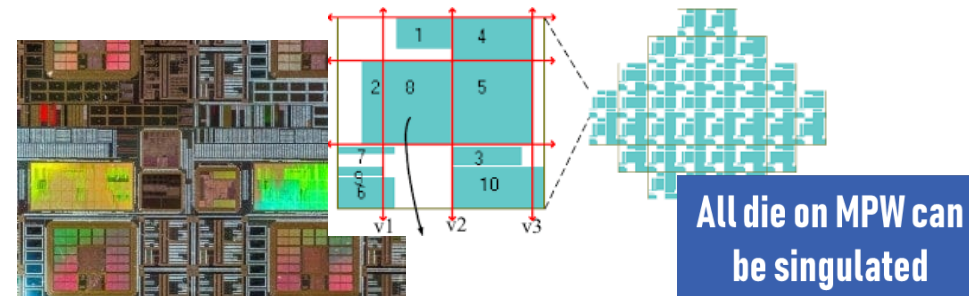
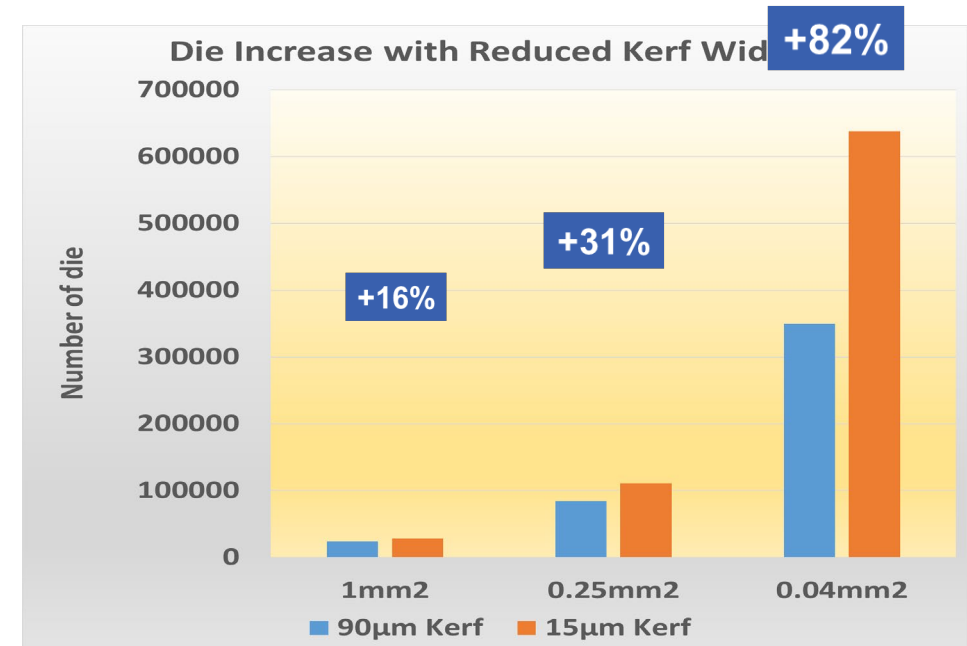
Wafer Layout Gains

Increasing die per wafer/reducing costs

- Narrower kerfs can be realised using Plasma Etch
 - $<10\mu\text{m}$
- More real estate for die
 - Guard Rings/Seal Rings can be shrunk/removed
- Inexpensive approach to increasing “fab capacity”
 - Reduce wafer costs
 - Reduce fab costs
- Multi-product Wafers
 - Where ALL die can be used

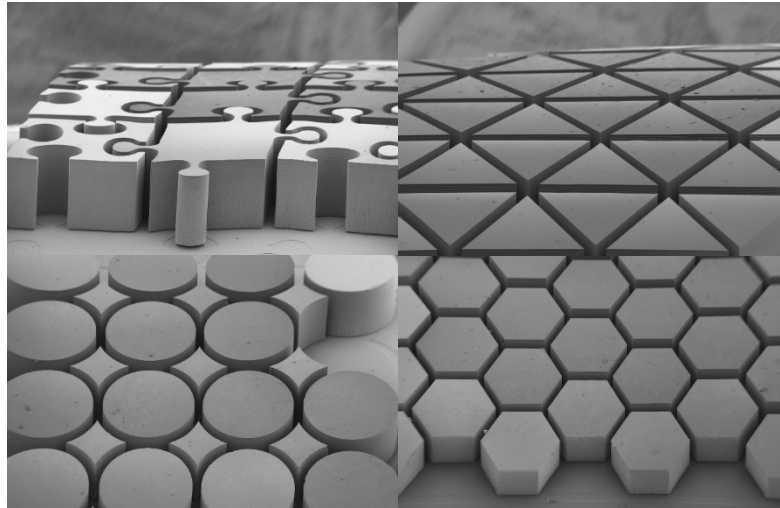


Guard Rings to prevent crack propagation are no longer required

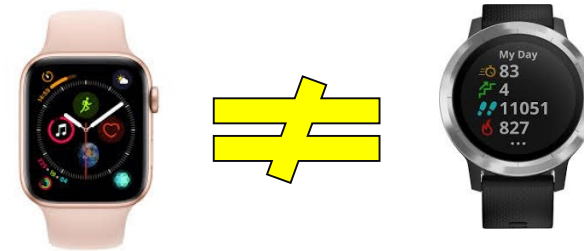


Form factor flexibility

- SiP allows minimised footprint for increased functionality
 - But design rules require minimum separation between die; 60µm
- Novel solutions may be required for best packing density



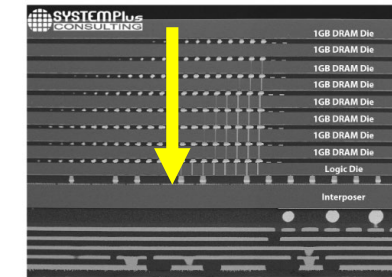
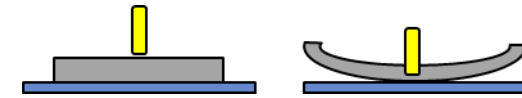
Examples of plasma diced structures
Mosaic & Rapier-S



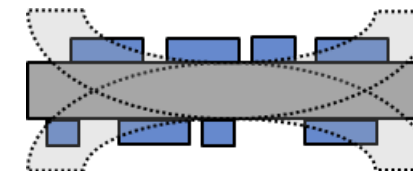
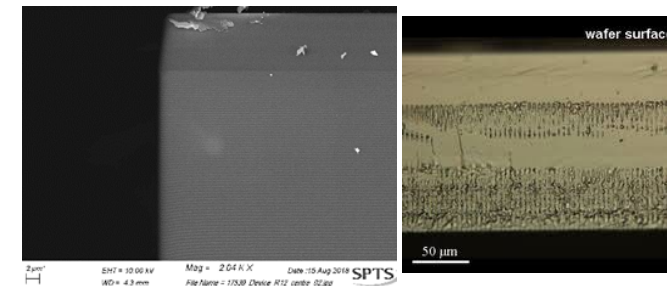
- Designers are able to take advantage of PD benefits
 - For both Product & Device

SiP Drivers for Plasma Dicing

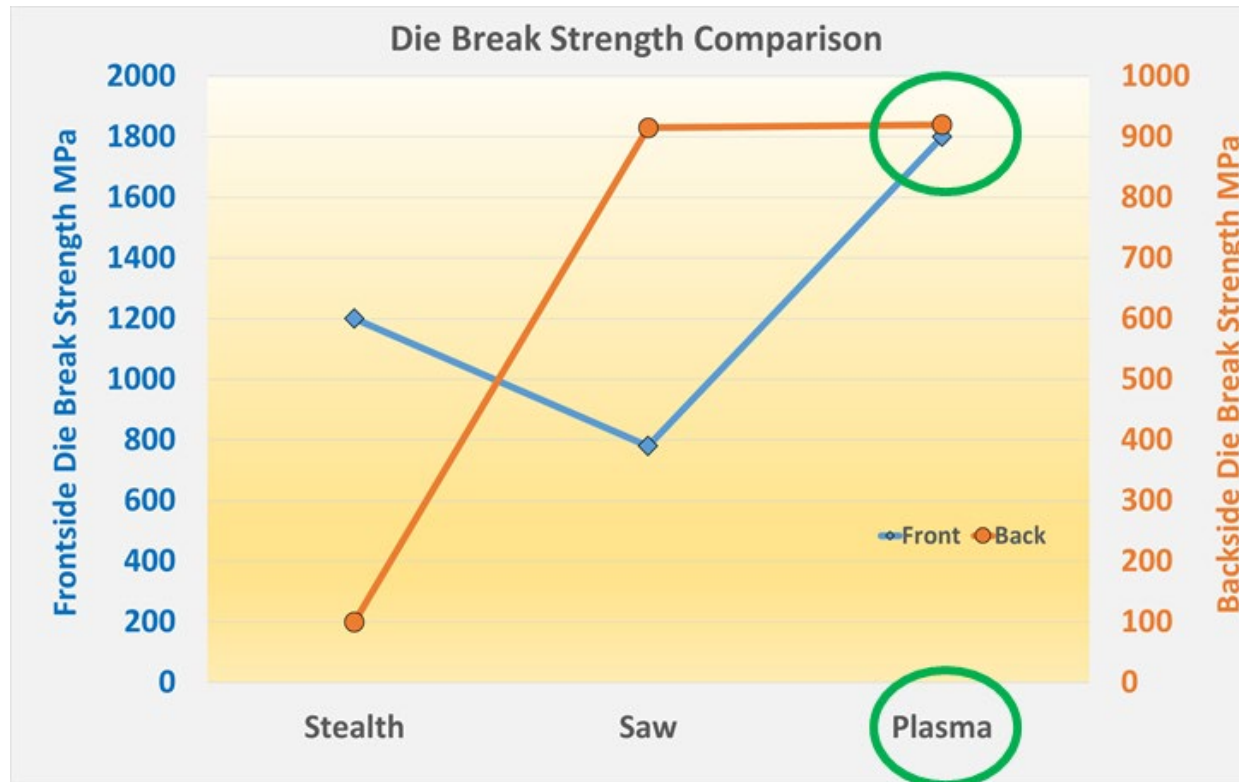
- Thinner Wafers
 - Singulation method critical to ensure no risk of in-service failure
- Stacked die
 - Pressures on die from stack stresses
 - Prevent particles from interfering with bonding; functionality
- Improving Yield at Singulation
 - Mechanical
 - Inspection
- Double sided SiP
 - Higher *Front and Back die strength* needed for dual plane deformation
- Automotive Reliability
 - ISO26262
 - Critical devices for ADAS need to cope with impacts, vibrations, etc



AMD Radeon Vega HBM2 Cross-Section



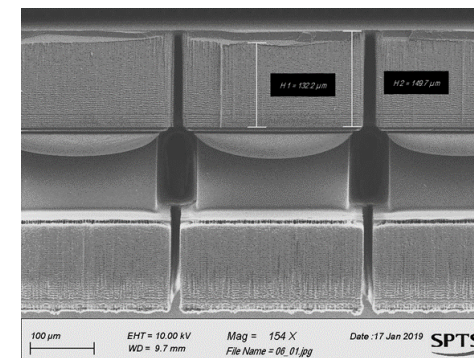
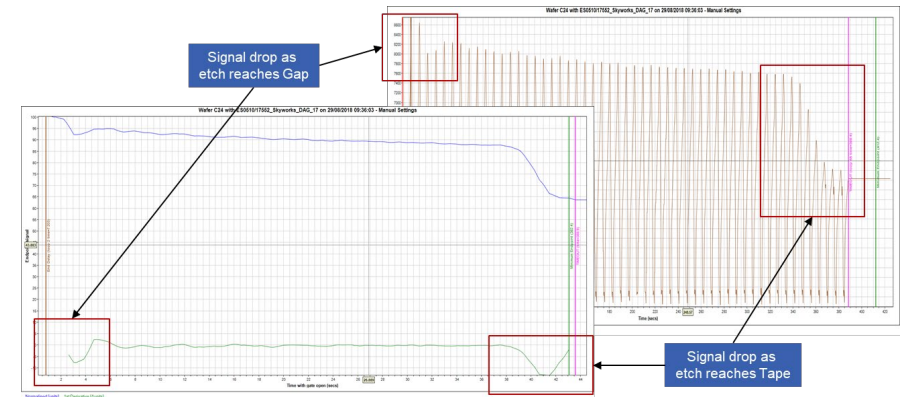
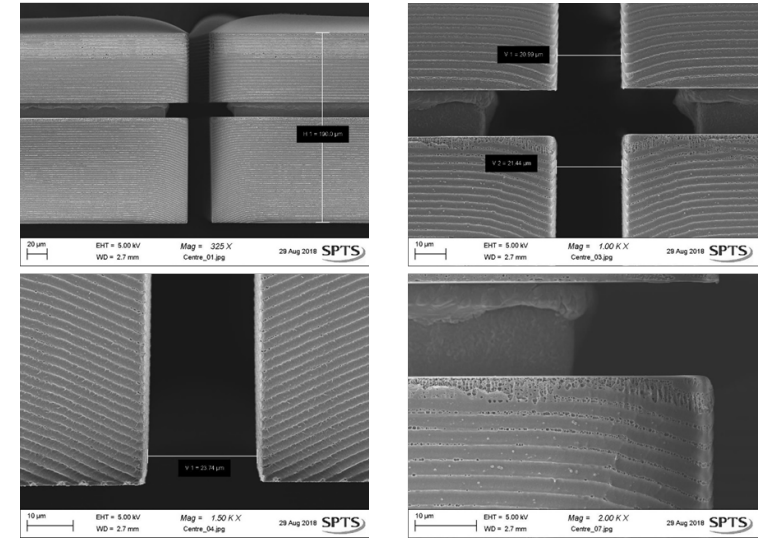
Achieving higher die break strength



- **No sidewall damage** at all due to chemical etch
- Preventing undercut (at tape) protects die strength gain
- Plasma is only method to improve front & back side strength

Filter Devices

- Small die size of filters (BAW) make them ideal candidates for plasma dicing
 - More filters being utilised in newer mobile phones
 - Increased die per wafer improves cost scenarios
- Filters are typically bonded wafer pairs
 - Plasma singulating stack of wafers
 - Avoids costly and time consuming individual die bonding
- Plasma etch through a void between wafers
 - Key is to manage protection of “exposed” Si during void transition
 - Examples shown with no impact on this region
 - Claritas can even detect when etch front traverses the void region
- DAG or DBG?
 - Both can be utilised for stacked wafers



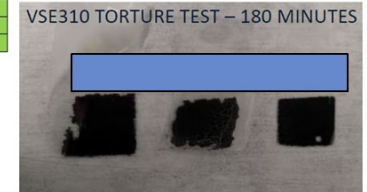
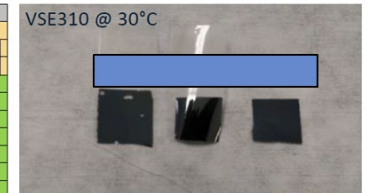
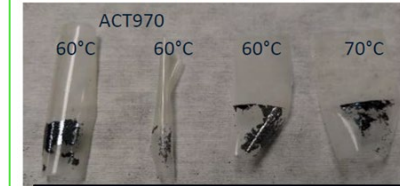
Defluorination & Strip

- To remove F and residual mask material
- LASER Coatings
 - Rinse off in DI H₂O
 - Plasma has **no impact** on solubility
- PR/Polymer
 - Wet...
 - Standard wet cleans can attack the tape
 - Versum → chemicals with no tape attack & no die loss
 - Dry...
 - O₂ dry strip with additional step to assist with F residue reduction
 - Reduces F levels to < control levels



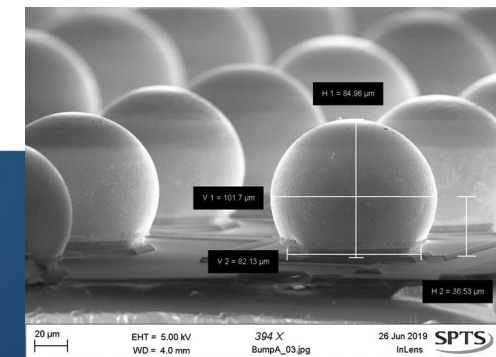
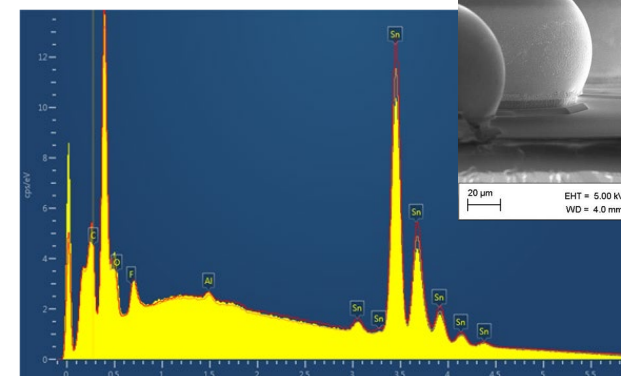
TAPE COMPATIBILITY SUMMARY

Time (min)	Estimated % Die Loss Over Time by Visual Observation					
	ACT970			VSE310		
1	0%	0%	0%	0%	0%	0%
3	0%	0%	0%	0%	0%	0%
5	0%	50%	0%	0%	0%	0%
7	10%	50%	0%	10%	0%	0%
10	10%	80%	0%	30%	0%	0%
13	20%		0%	30%	0%	0%
16	20%		0%	60%	0%	0%
18	50%		0%	0%	0%	0%
20	50%		40%	0%	0%	0%
180	VSE310 torture test			10%	10%	<10%



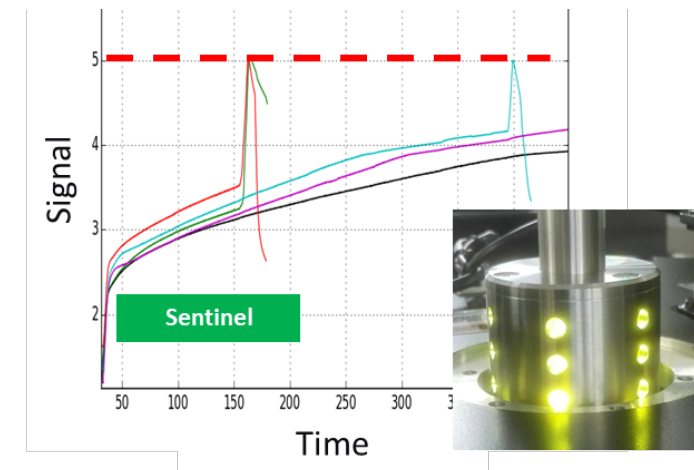
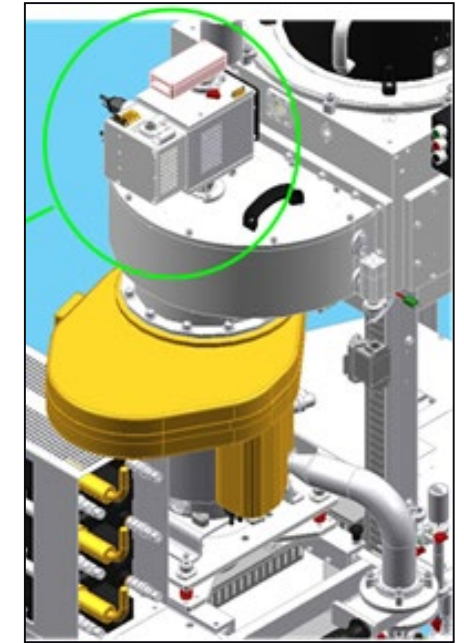
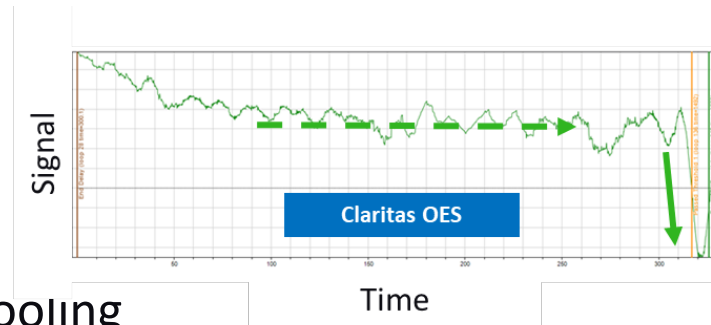
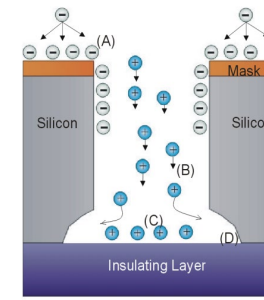
SIGNIFICANTLY LESS TAPE DEFORMATION AND DIE LOSS WAS SEEN WITH VSE310

Joint paper at Semicon Europa 2018



Safe-guarding High Value Wafers

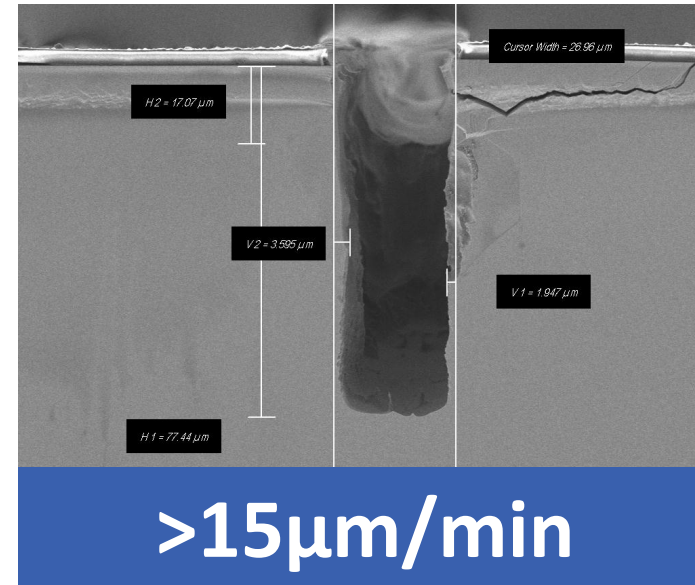
- Claritas end-point detection
 - Sensitive OES EPD (<0.05% OA; >100mT process pressures)
 - Minimal over-etching; Maximises throughput
 - Minimises notching
 - → Maximises die strength
- Sentinel™ monitors substrate & alerts for loss of cooling
 - Tape and taping quality
 - Allows intervention & re-work



SENTINEL™ & CLARITAS™ ARE UNIQUE TO SPTS

GaAs Dicing

- Running framed GaAs wafers on GaAs dicing process module
 - Using Si DRIE experience to produce high rate GaAs etching
- Consolidating process window
 - Considering chemistries away from traditional applications
- Integration is a factor as per Si
 - Learning from GaAs BSV being applied
- Approx 1.5x throughput c/w LASER
 - Based on ~15min LASER singulation time
 - LASER yield loss >1k ppm due to damage
 - Expect plasma to avoid this
 - Work ongoing...
- Wider process flow discussions still needed
 - Frames vs Carrier wafers; DAG vs DBG
 - This applies to other III-V materials; low volatility compounds (SiC, Glass, etc) – not suited to frames
- Paper on this topic was accepted for CS Mantech, so we will find another outlet for that later in the year



Summary

- Plasma dicing is very much here to stay
 - Benefits are clear and obvious
 - All potential barriers now have solutions; including fluorine
- Massive interest
 - Across the entire industry & markets; it is not just a die per wafer play
- Modest growth to date because Semi Industry is very conservative
 - Anxiety to move away from embedded processes and infrastructure
 - Education and experience is key to managing this
 - Plasma Dicing continues to be our largest and most subscribed demo activity
- More drivers are setting the momentum
 - SiP, Filters, HBW along with the demand for smaller die
 - GaAs
- Don't forget plasma dicing before grind (DBG)
 - Same integration activities, wider material opportunities

For more information

- Thank you for your attention!
 - Email enquiries@spts.com
 - Keep up-to-date with SPTS @ www.spts.com



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https://twitter.com/SPTS_Tech

Web Resources @www.spts.com

The screenshot displays the SPTS website's resource page. It features a navigation menu with links for Home, About Us, Products, Services, and Contact Us. The main content area is divided into two columns. The left column includes a large image of a plasma dielectric coating process, followed by a section titled 'Plasma Dielectric' with a brief description and a 'Why use Plasma Dielectric?' section. The right column is titled 'Application Briefs' and contains several cards for different technologies: 'Production to Scale', 'Blocker Sinter Die', 'FDWLP - FPD Processors', and 'High Productivity USM/JC'. At the bottom of the page, there are two main resource categories: 'Tech Insights' with a link to <http://www.spts.com/tech-insights> and 'Application Briefs' with a link to <http://www.spts.com/resources/literature-library>. The SPTS logo is visible in the bottom right corner of the screenshot.

- Tech Insights
 - <http://www.spts.com/tech-insights>
- Application Briefs
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Questions?

